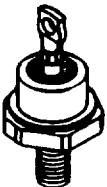
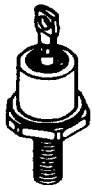
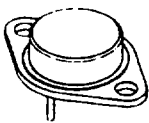
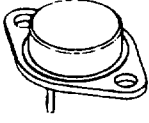


ULTRA-FAST
RECTIFIERS

PACKAGE	DEVICE TYPE	PIV VOLTS	I _F (avg) AMPS	V _F @ I _F (avg) VOLTS	t _{rr} nsec	∅ _{j/c} °C/W
DO-5 	NES501	50	50@125°C	.95	50	1.0
	NES502	75	50@125°C	.95	50	1.0
	NES503	100	50@125°C	.95	50	1.0
	NES504	125	50@125°C	.95	50	1.0
	NES505	150	50@125°C	.95	50	1.0
	NES801	50	70@100°C	.975	50	0.8
	NES802	100	70@100°C	.975	50	0.8
NES803	150	70@100°C	.975	50	0.8	
DO-4 	NES701	50	25@100°C	.95	35	1.5
	NES702	100	25@100°C	.95	35	1.5
	NES703	150	25@100°C	.95	35	1.5
	NES704	200	20@100°C	1.25	50	1.5
	IN5812	50	20@100°C	0.9@10A	15	3.0
	IN5813	75	20@100°C	0.9@10A	15	3.0
	IN5814	100	20@100°C	0.9@10A	15	3.0
	IN5815	125	20@100°C	0.9@10A	15	3.0
IN5816	150	20@100°C	0.9@10A	15	3.0	
TO-3 	NES601	50	30@100°C	.915	50	1.0
	NES602	100	30@100°C	.915	50	1.0
	NES603	150	30@100°C	.915	50	1.0


CENTER TAP

TO-3 	NES2601	50	30@100°C	.93@15A	35	1.0
	NES2602	100	30@100°C	.93@15A	35	1.0
	NES2603	150	30@100°C	.93@15A	35	1.0

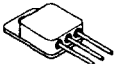
* T_C = 25°C

NEW ENGLAND SEMICONDUCTOR

ULTRA-FAST RECTIFIERS

PACKAGE	DEVICE TYPE	I_F (avg) AMPS $T_C = 100^\circ\text{C}$	V_{RMM} VOLTS $T_J = 100^\circ\text{C}$	V_F VOLTS $T_J = 100^\circ\text{C}$	I_R AMPS	t_{rr} ns
2 LEAD HERMETIC 	NPD1505	15	50	0.9	0.001	35
	NPD1510	15	100	0.9	0.001	35
	NPD1515	15	150	0.9	0.001	35
	NPD1520	15	200	0.9	0.001	35
	NPD1530	15	300	1.15	0.001	35
	NPD1540	15	400	1.15	0.001	35
	NPD1550	15	500	1.4	0.002	50
	NPD1560	15	600	1.4	0.002	50

CENTER TAP

TO-257 	NPD1505C	7.5	50	1.0	0.001	35
	NPD1510C	7.5	100	1.0	0.001	35
	NPD1515C	7.5	150	1.0	0.001	35
	NPD1520C	7.5	200	1.0	0.001	35
	NPD1530C	7.5	300	1.25	0.001	35
	NPD1540C	7.5	400	1.25	0.001	35
	NPD1550C	7.5	500	1.5	0.002	60
	NPD1560C	7.5	600	1.5	0.002	60

* Electrical Characteristics @ 25°C unless otherwise noted
Specifications per diode